

HAT2202C

Silicon N Channel MOS FET Power Switching

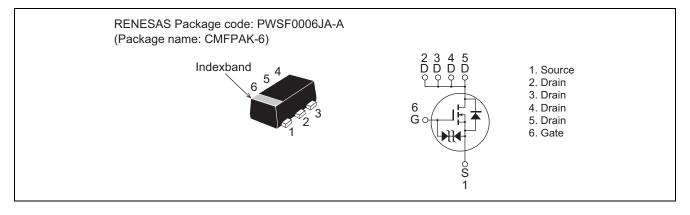
REJ03G1236-0600 Rev.6.00 Oct 01, 2009

 $(T_{0} - 25^{\circ}C)$

Features

- Low on-resistance $R_{DS(on)} = 31 \text{ m}\Omega \text{ typ.} (at V_{GS} = 4.5 \text{ V})$
- Low drive current.
- High density mounting
- 2.5 V gate drive devices.

Outline



Absolute Maximum Ratings

		$(1a = 25^{\circ}C)$
Symbol	Ratings	Unit
V _{DSS}	20	V
V _{GSS}	±12	V
I _D	3	A
I _D (pulse) ^{Note1}	12	A
I _{DR}	3	A
Pch ^{Note 2}	900	mW
Tch	150	°C
Tstg	-55 to +150	°C
	VDSS VGSS ID ID ID ID IDR PchNote 2 Tch	V _{DSS} 20 V _{GSS} ±12 I _D 3 I _D (pulse) ^{Note1} 12 I _{DR} 3 Pch ^{Note 2} 900 Tch 150

Notes: 1. $PW \leq$ 10 $\mu s,\,duty\,cycle \leq$ 1%

2. When using the glass epoxy board. (FR4 40 \times 40 \times 1.6 mm)

Electrical Characteristics

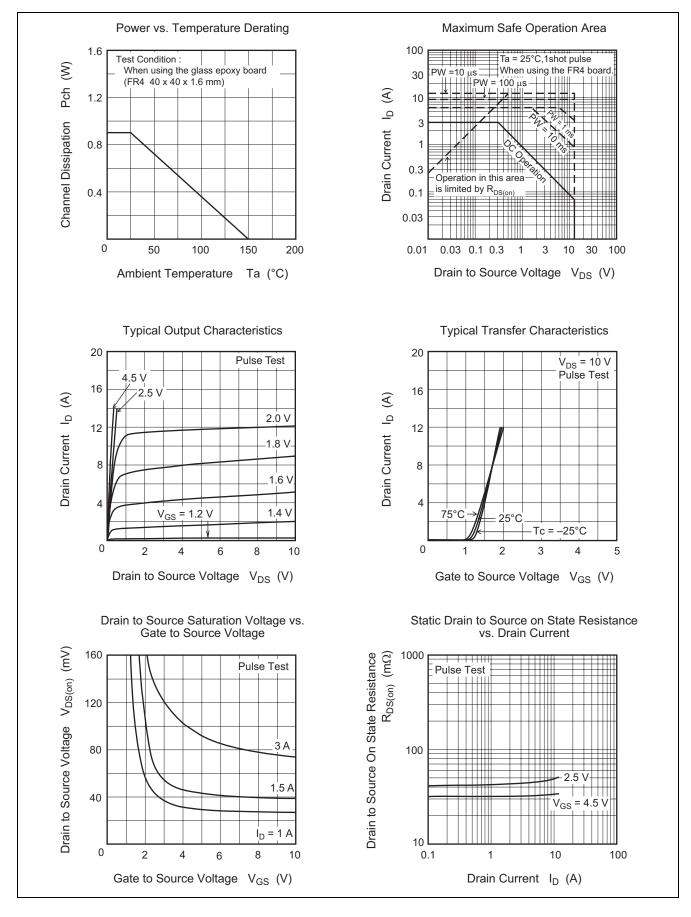
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						(Ta = 25°C)
ltem	Symbol	Min	Тур	Max	Unit	Test Conditions
Drain to Source breakdown voltage	V _{(BR)DSS}	20	_	—	V	I _D = 10 mA, V _{GS} = 0
Gate to Source breakdown voltage	V _{(BR)GSS}	±12	_	—	V	$I_{G} = \pm 100 \ \mu A, V_{DS} = 0$
Gate to Source leakage current	I _{GSS}	_	_	±10	μA	V_{GS} = \pm 10V, V_{DS} = 0
Drain to Source leakage current	I _{DSS}	_	_	1	μA	$V_{DS} = 20 V, V_{GS} = 0$
Gate to Source cutoff voltage	V _{GS(th)}	0.4	_	1.4	V	I _D = 10 V, I _D = 1 mA
Drain to Source on state resistance	R _{DS(on)}	_	31	40	mΩ	I_D = 1.5 A, V_{GS} =4.5 V ^{Note3}
		_	43	55	mΩ	I_D = 1.5 A, V_{GS} = 2.5 V ^{Note3}
Forward transfer admittance	y _{fs}	6.5	9.5	_	S	I_D = 1.5 A, V_{DS} = 10 V ^{Note3}
Input capacitance	Ciss	_	520	_	pF	V_{DS} = 10 V, V_{GS} = 0,
Output capacitance	Coss	_	115	_	pF	f = 1 MHz
Reverse transfer capacitance	Crss		60		pF	1
Total gate charge	Qg		6		nC	V_{DD} = 10 V, V_{GS} = 4.5 V,
Gate to Source charge	Qgs	_	1	_	nC	I _D = 3 A
Gate to Drain charge	Qgd	_	1.4	_	nC	
Turn - on delay time	t _{d(on)}	_	9	_	ns	I _D = 1.5 A,
Rise time	tr	_	8	_	ns	V_{GS} = 10 V, V_{DD} =10 V,
Turn - off delay time	t _{d(off)}	_	28		ns	R _L = 6.7 Ω, R _g = 4.7 Ω
Fall time	t _f	_	6		ns]
Body - Drain diode forward voltage	V _{DF}	_	0.8	1.1	V	$I_F = 3 \text{ A}, V_{GS} = 0^{\text{Note3}}$

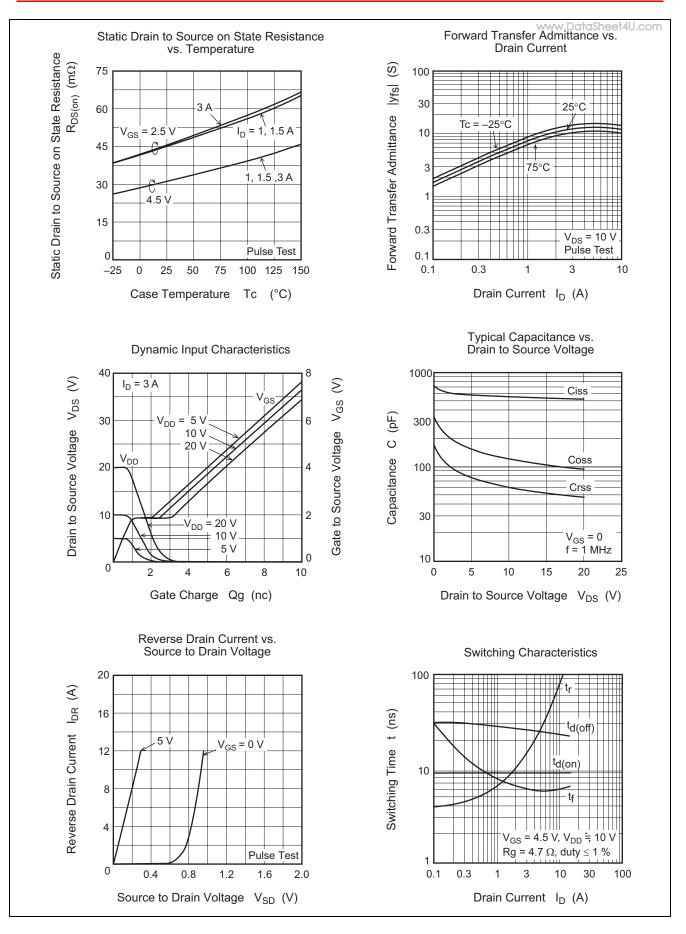
Notes: 3. Pulse test



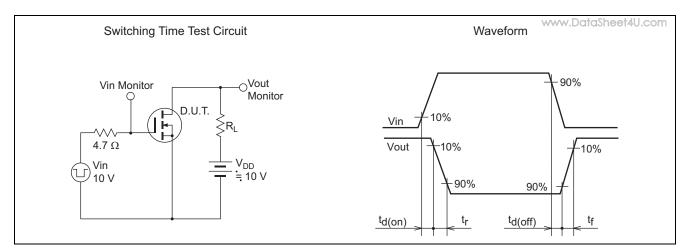
Main Characteristics







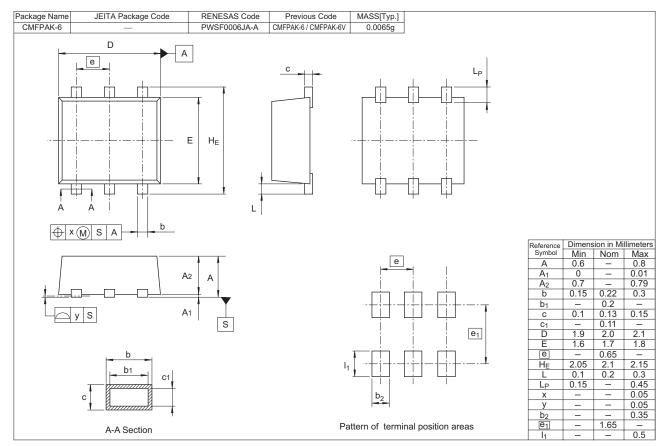
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Package Dimensions

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Ordering Information

Part No.	Quantity	Shipping Container
HAT2202C-EL-E	3000 pcs	Taping



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